

View Online at <https://aerobasegroup.com/nsn/5961-01-168-6508>

Inclosure Material:

Metal all transistor

Overall Length:

1.573 inches all transistor

Overall Height:

0.380 inches all transistor

Overall Width:

1.050 inches all transistor

Mounting Facility Quantity:

2 all transistor

Internal Configuration:

Junction contact all transistor

Electrode Internally-electrically Connected To Case:

Collector all transistor

Response Time:

0.6 microseconds all transistor

Internal Junction Configuration:

Npn all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Unthreaded hole all transistor

Field Force Effect Type:

Electrostatic charge

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

650.0 collector to base voltage/static/emitter open all transistor and 650.0 collector to emitter voltage, dc with specified circuit between base and emitter all transistor and 400.0 collector to emitter voltage/static/base open all transistor and 8.0 emitter to base voltage, static, collector open all transistor

Current Rating Per Characteristic:

5.00 amperes source cutoff current all transistor and 15.00 amperes source cutoff current all transistor

Power Rating Per Characteristic:

175.0 watts small-signal input power, common-collector preset all transistor

Maximum Operating Temperature Per Measurement Point:

200.0 degrees celsius ambient air all transistor

Test Data Document:

94117-1064780 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

2 pin all transistor and 1 case all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0